

HS-139RH, HS-139EH

Radiation Hardened Quad Voltage Comparator

The Radiation Hardened HS-139RH, HS-139EH consists of four independent single or dual supply voltage comparators on a single monolithic substrate. The common mode input voltage range includes ground, even when operated from a single supply and the low supply current makes these comparators suitable for low power applications. These types were designed to directly interface with TTL and CMOS.

The HS-139RH, HS-139EH are fabricated on our dielectrically isolated Rad Hard Silicon Gate (RSG) process, which provides an immunity to Single Event Latch-up and the capability of highly reliable performance in any radiation environment.

Specifications for Rad Hard QML devices are controlled by the Defense Logistics Agency Land and Maritime (DLA). The SMD numbers listed below must be used when ordering.

Detailed Electrical Specifications for the HS-139RH, HS-139EH are contained in [SMD 5962-98613](#). A "hot-link" is provided on our homepage with instructions for downloading.

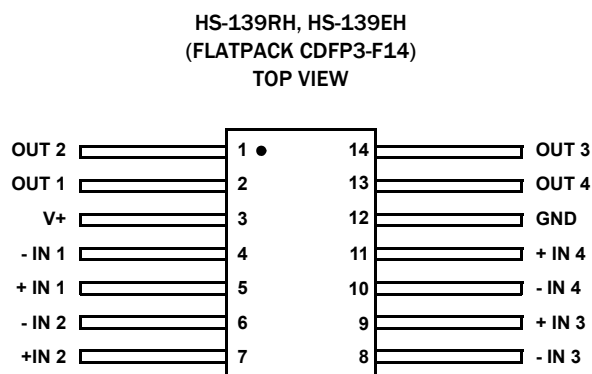
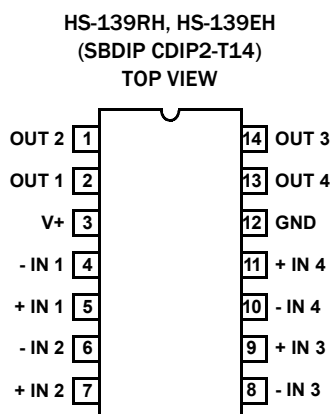
Features

- QML qualified per MIL-PRF-38535 requirements
- Radiation environment
 - Latch-up free under any conditions
 - Total dose (Max). 3×10^5 RAD(Si)
 - SEU LET threshold 20MeV/cm²/mg
 - Low dose rate effects immunity
- 100V output voltage withstand capability
- ESD protection to >3000V
- Differential input voltage range equal to the supply voltage
- Input offset voltage (V_{IO}) 2mV (Max)
- Quiescent supply current 2mA (Max)
- Pb-Free (RoHS Compliant)

Applications

- Pulse generators
- Timing circuitry
- Level shifting
- Analog-to-digital conversion

Pin Configurations



Ordering Information

ORDERING SMD NUMBER (Note 1)	PART NUMBER (Note 2)	PACKAGE DESCRIPTION (RoHS Compliant)	PKG. DWG. #	CARRIER TYPE	TEMP. RANGE (°C)
5962F9861303VCC	HS1-139EH-Q	14 Ld SBDIP	D14.3	Tube	-55 to +125
5962F9861301VCC	HS1-139RH-Q	14 Ld SBDIP	D14.3	Tube	-55 to +125
5962F9861301QCC	HS1-139RH-8	14 Ld SBDIP	D14.3	Tube	-55 to +125
HS1-139RH/PROTO (Note 3)	HS1-139RH/PROTO	14 Ld SBDIP	D14.3	Tube	-55 to +125
5962F9861301VXC	HS9-139RH-Q	14 Ld FLATPACK	K14.A	Tray	-55 to +125
5962F9861301QXC	HS9-139RH-8	14 Ld FLATPACK	K14.A	Tray	-55 to +125
5962F9861303VXC	HS9-139EH-Q	14 Ld FLATPACK	K14.A	Tray	-55 to +125
HS9-139RH/PROTO (Note 3)	HS9-139RH/PROTO	14 Ld FLATPACK	K14.A	Tray	-55 to +125
5962F9861303V9A (Note 4)	HS0-139EH-Q	Die	N/A	N/A	-55 to +125
5962F9861301V9A (Note 4)	HS0-139RH-Q	Die	N/A	N/A	-55 to +125
HS0-139RH/SAMPLE (Notes 3, 4)	HS0-139RH/SAMPLE	Die	N/A	N/A	-55 to +125

NOTES:

1. Specifications for Rad Hard QML devices are controlled by the Defense Logistics Agency Land and Maritime (DLA). The SMD numbers listed in the table must be used when ordering.
2. These Pb-free Hermetic packaged products employ 100% Au plate - e4 termination finish, which is RoHS compliant and compatible with both SnPb and Pb-free soldering operations.
3. The /PROTO and /SAMPLE are not rated or certified for Total Ionizing Dose (TID) or Single Event Effect (SEE) immunity. These parts are intended for engineering evaluation purposes only. The /PROTO parts meet the electrical limits and conditions across temperature specified in the DLA SMD and are in the same form and fit as the qualified device. The /SAMPLE parts are capable of meeting the electrical limits and conditions specified in the DLA SMD. The /SAMPLE parts do not receive 100% screening across temperature to the DLA SMD electrical limits. These part types do not come with a Certificate of Conformance because they are not DLA qualified devices.
4. Die product tested at $T_A = +25^{\circ}\text{C}$. The wafer probe test includes functional and parametric testing sufficient to make the die capable of meeting the electrical performance outlined in SMD.

Die Characteristics

DIE DIMENSIONS:

3750 μ m x 2820 μ m (148 mils x 111 mils)
483 μ m \pm 25.4 μ m (19 mils \pm 1 mil)

INTERFACE MATERIALS:

Glassivation:

Type: Silox (SiO₂)
Thickness: 8.0kÅ \pm 1.0kÅ

Top Metallization:

Type: AlSiCu
Thickness: 16.0kÅ \pm 2kÅ

Substrate:

Radiation Hardened Silicon Gate, Dielectric Isolation

Backside Finish:

Silicon

ASSEMBLY RELATED INFORMATION:

Substrate Potential:

Unbiased (DI)

ADDITIONAL INFORMATION:

Worst Case Current Density:

$<2.0 \times 10^5$ A/cm²

Transistor Count:

49

Metallization Mask Layout

HS-139RH, HS-139EH

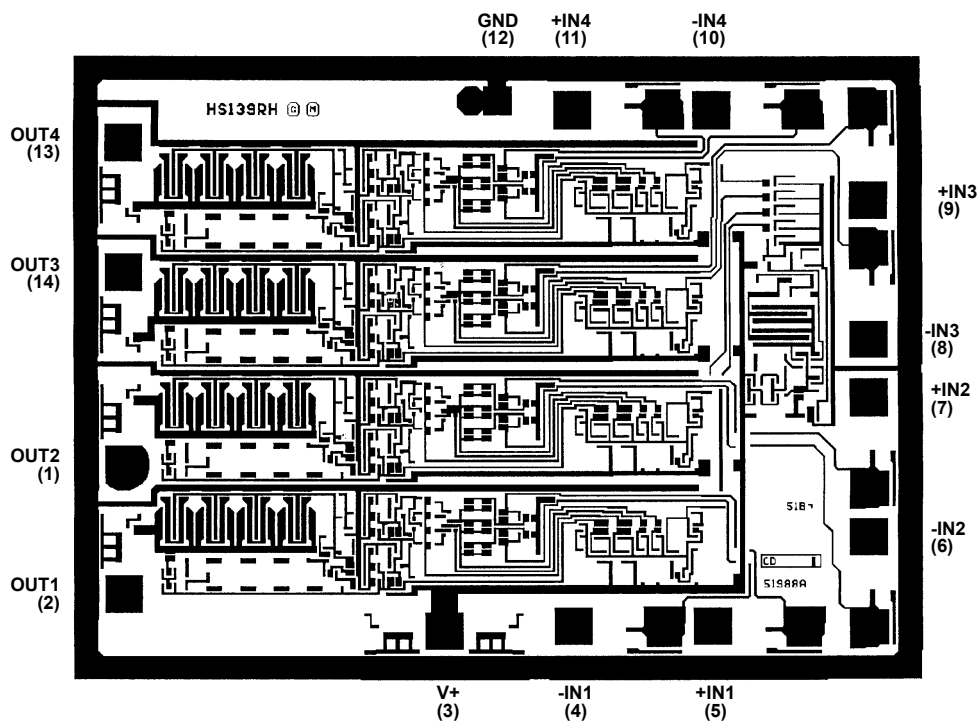


TABLE 1. HS-139RH, HS-139EH PAD COORDINATES

PIN NUMBER	PAD NAME	RELATIVE TO PIN 1	
		X COORDINATES	Y COORDINATES
1	OUT 2	0	0
2	OUT 1	0	-535
3	V+	1323	-688
4	-IN 1	1862	-670
5	+IN 1	2439	-670
6	-IN 2	3084	-299
7	+IN 2	3084	278
8	-IN 3	3084	518
9	+IN 3	3084	1095
10	-IN 4	2439	1466
11	+IN 4	1862	1466
12	GND	1550	1503
13	OUT 4	0	1331
14	OUT 3	0	796

NOTE: Dimensions in microns

Package Outline Drawings

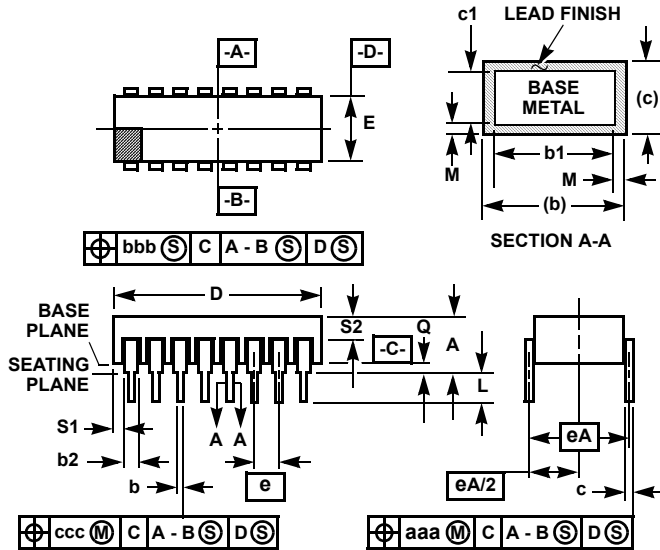
The package outline drawings are located at the end of this document and are accessible from the Renesas website. The package information is the most current data available and is subject to change without revision of this document.

Revision History

REVISION	DATE	DESCRIPTION
6.01	May 5, 2025	<p>Updated Ordering Information table notes.</p> <p>Added Revision History Section.</p> <p>Updated POD K14.A to the latest revision; changes are as follows:</p> <ul style="list-style-type: none"> -Applied latest template -Corrected typo in the mm value for dimension E1 from 7.11 to 7.37mm (i.e. the dim equivalent to E1 from the table in the previous revision) to make it equal to the 0.290 inch dim & compliant to MIL-STD-1835. -Corrected typo in the dimension of the bottom ceramic pedestal width.

Hermetic Packages for Integrated Circuits

Ceramic Dual-In-Line Metal Seal Packages (SBDIP)



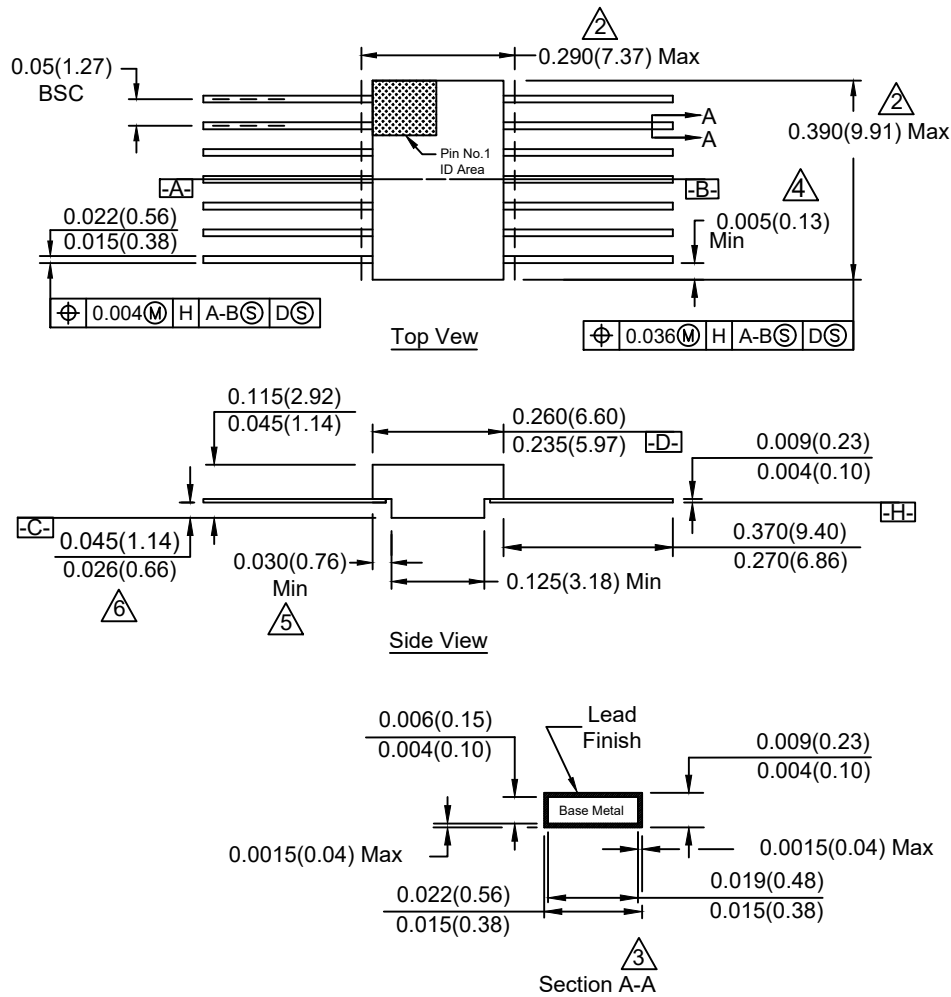
NOTES:

1. Index area: A notch or a pin one identification mark shall be located adjacent to pin one and shall be located within the shaded area shown. The manufacturer's identification shall not be used as a pin one identification mark.
2. The maximum limits of lead dimensions b and c or M shall be measured at the centroid of the finished lead surfaces, when solder dip or tin plate lead finish is applied.
3. Dimensions b1 and c1 apply to lead base metal only. Dimension M applies to lead plating and finish thickness.
4. Corner leads (1, N, N/2, and N/2+1) may be configured with a partial lead paddle. For this configuration dimension b3 replaces dimension b2.
5. Dimension Q shall be measured from the seating plane to the base plane.
6. Measure dimension S1 at all four corners.
7. Measure dimension S2 from the top of the ceramic body to the nearest metallization or lead.
8. N is the maximum number of terminal positions.
9. Braze fillets shall be concave.
10. Dimensioning and tolerancing per ANSI Y14.5M - 1982.
11. Controlling dimension: INCH.

D14.3 MIL-STD-1835 CDIP2-T14 (D-1, Configuration C) 14 Lead Ceramic Dual In-Line Metal Seal Package

SYMBOL	INCHES		MILLIMETERS		NOTES
	MIN	MAX	MIN	MAX	
A	-	0.200	-	5.08	-
b	0.014	0.026	0.36	0.66	2
b1	0.014	0.023	0.36	0.58	3
b2	0.045	0.065	1.14	1.65	-
b3	0.023	0.045	0.58	1.14	4
c	0.008	0.018	0.20	0.46	2
c1	0.008	0.015	0.20	0.38	3
D	-	0.785	-	19.94	-
E	0.220	0.310	5.59	7.87	-
e	0.100 BSC		2.54 BSC		-
eA	0.300 BSC		7.62 BSC		-
eA/2	0.150 BSC		3.81 BSC		-
L	0.125	0.200	3.18	5.08	-
Q	0.015	0.060	0.38	1.52	5
S1	0.005	-	0.13	-	6
S2	0.005	-	0.13	-	7
α	90°	105°	90°	105°	-
aaa	-	0.015	-	0.38	-
bbb	-	0.030	-	0.76	-
ccc	-	0.010	-	0.25	-
M	-	0.0015	-	0.038	2
N	14		14		8

Rev. 0 4/94



Notes:

- 1 Index area: A notch or a pin one identification mark shall be located adjacent to pin one and shall be located within the shaded area shown. The manufacture's identification shall not be used as a pin one identification mark.
- 2 This dimension allows for off-center lid, meniscus, and glass overrun.
- 3 The maximum limits of lead dimensions (section A-A) shall be measured at the centroid of the finished lead surfaces, when solder dip or tin plate finish is applied.
- 4 Measure dimension at all four corners.
- 5 For bottom-brazed lead packages, no organic or polymeric materials shall be molded to the bottom of the package to cover the leads.
- 6 This dimension shall be measured at the point of exit (beyond the meniscus) of the lead from the body. This dimension's minimum shall be reduced by 0.0015 inch (0.038mm) maximum when solder dip lead finish is applied.
7. Dimensioning and tolerancing per ANSI Y14.5M - 1982.
8. Dimensions: INCH(mm). Controlling dimension: INCH.
9. Compliant to MIL-STD-1835 CDFP3-F14 (F-2A, CONFIGURATION B).

IMPORTANT NOTICE AND DISCLAIMER

RENESAS ELECTRONICS CORPORATION AND ITS SUBSIDIARIES ("RENESAS") PROVIDES TECHNICAL SPECIFICATIONS AND RELIABILITY DATA (INCLUDING DATASHEETS), DESIGN RESOURCES (INCLUDING REFERENCE DESIGNS), APPLICATION OR OTHER DESIGN ADVICE, WEB TOOLS, SAFETY INFORMATION, AND OTHER RESOURCES "AS IS" AND WITH ALL FAULTS, AND DISCLAIMS ALL WARRANTIES, EXPRESS OR IMPLIED, INCLUDING, WITHOUT LIMITATION, ANY IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE, OR NON-INFRINGEMENT OF THIRD-PARTY INTELLECTUAL PROPERTY RIGHTS.

These resources are intended for developers who are designing with Renesas products. You are solely responsible for (1) selecting the appropriate products for your application, (2) designing, validating, and testing your application, and (3) ensuring your application meets applicable standards, and any other safety, security, or other requirements. These resources are subject to change without notice. Renesas grants you permission to use these resources only to develop an application that uses Renesas products. Other reproduction or use of these resources is strictly prohibited. No license is granted to any other Renesas intellectual property or to any third-party intellectual property. Renesas disclaims responsibility for, and you will fully indemnify Renesas and its representatives against, any claims, damages, costs, losses, or liabilities arising from your use of these resources. Renesas' products are provided only subject to Renesas' Terms and Conditions of Sale or other applicable terms agreed to in writing. No use of any Renesas resources expands or otherwise alters any applicable warranties or warranty disclaimers for these products.

(Disclaimer Rev.1.01)

Corporate Headquarters

TOYOSU FORESIA, 3-2-24 Toyosu,
Koto-ku, Tokyo 135-0061, Japan
www.renesas.com

Contact Information

For further information on a product, technology, the most up-to-date version of a document, or your nearest sales office, please visit www.renesas.com/contact-us/.

Trademarks

Renesas and the Renesas logo are trademarks of Renesas Electronics Corporation. All trademarks and registered trademarks are the property of their respective owners.